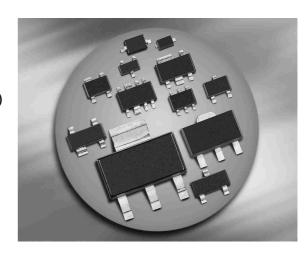


## **Silicon Variable Capacitance Diode**

- For FM radio tuner with extended frequency band
- High tuning ratio at low supply voltage (car radio)
- Monolitic chip (common cathode)
   for perfect dual diode tracking
- Good linearity for C- V curve
- High figure of merit



#### **BB914**



Туре	Package	Configuration	<b>L</b> <sub>S</sub> (nH)	Marking
BB914	SOT23	common cathode	1.8	SM

# **Maximum Ratings** at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V <sub>R</sub>	18	V
Peak reverse voltage	$V_{\rm RM}$	20	
$(R \ge 5k\Omega)$			
Forward current	I <sub>F</sub>	50	mA
Operating temperature range	$T_{op}$	-55 125	°C
Storage temperature	$T_{\rm stg}$	-55 150	



**Electrical Characteristics** at  $T_A$  = 25°C, unless otherwise specified

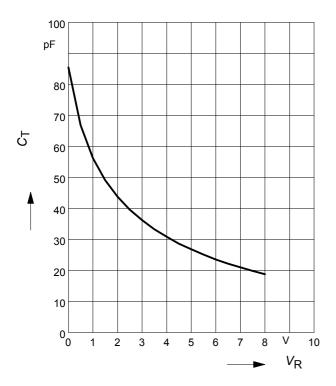
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	·				
Reverse current	$I_{R}$	-	-		nA
<i>V</i> <sub>R</sub> = 16 V		-	-	20	
$V_{\rm R}$ = 16 V, $T_{\rm A}$ = 85 °C				200	
AC Characteristics					
Diode capacitance	C <sub>T</sub>				pF
$V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$		42.5	43.75	45	
$V_{R} = 8 \text{ V}, f = 1 \text{ MHz}$		17.6	18.7	19.75	
Capacitance ratio	$C_{T2}/C_{T8}$	2.28	2.34	2.42	
$V_{R} = 2 \text{ V}, V_{R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching <sup>1)</sup>	$\Delta C_{T}/C_{T}$	-	-	1.5	%
$V_{R} = 2 \text{ V}, V_{R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	$r_{\rm S}$	-	0.28		Ω
$V_{R}$ = 2 V, $f$ = 100 MHz					

<sup>&</sup>lt;sup>1</sup>For details please refer to Application Note 047.



# Diode capacitance $C_T = f(V_R)$

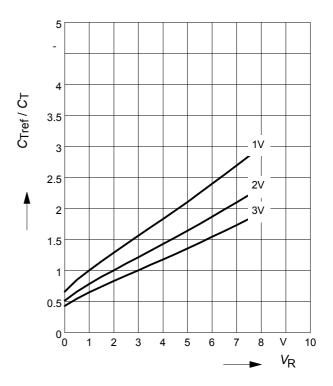
f = 1MHz



# Capacitance ratio $C_{\text{Tref}}/C_{\text{T}} = f(V_{\text{R}})$

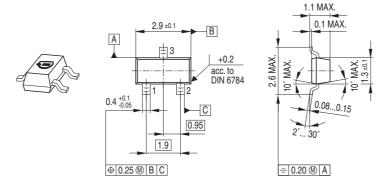
f = 1MHz

3

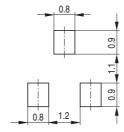




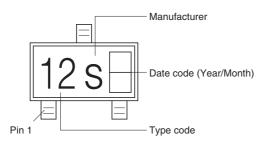
## Package Outline

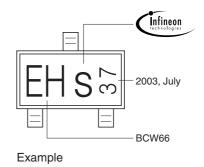


### Foot Print



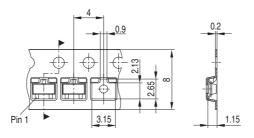
## Marking Layout





## Packing

Code E6327: Reel ø180 mm = 3.000 Pieces/Reel Code E6433: Reel ø330 mm = 10.000 Pieces/Reel





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